



210096US-2

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF: :
TOSHIAKI SHINOHARA : GROUP ART UNIT: 2811
SERIAL NO: 09/895,025 :
FILED: JULY 2, 2001 : EXAMINER: VU, Q.
FOR: SEMICONDUCTOR DEVICE

RECEIVED
OCT 21 2002
TECHNOLOGY CENTER 2800

#7/Amend A
H. Adam
10/28/02

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

In response to the Official Action mailed July 18, 2002, please amend this application
as follows:

IN THE ABSTRACT

Please amend the Abstract at page 23, lines 3-17 to read as follows:¹

M
It is an object to provide a semiconductor device having an improved heat dissipation
characteristic. A power element is mounted on and jointed and to a metal block through a
jointing material. An insulating substrate includes a ceramic substrate and metal layers
formed on both surfaces of the ceramic substrate and having thicknesses equal to each other.
The metal block and the insulating substrate are provided per insulation unit of the power
element. The metal layer of the insulating substrate is joined to a surface of the metal block
through a jointing material opposite to a surface thereof for forming the power element. An
electrode terminal is attached to a surface of the metal block having a power element joined

¹A marked-up copy of the changes made to the Abstract is attached.